

-	1910	"semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:01
-	1910	"semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:01
-	53714	barrier adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:02
-	65	"semiconductor energy laboratory" and (barrier adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:24
-	3430	crystallization and (tft or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:26
-	318636	nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:26
-	1134	(crystallization and (tft or thin adj film adj transistor)) and nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:27
-	6040	gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:27
-	369	((crystallization and (tft or thin adj film adj transistor)) and nickel) and gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:27
-	91222	silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:28
-	333	((((crystallization and (tft or thin adj film adj transistor)) and nickel) and gettering) and (silicon adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:38
-	5036	Joo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:38
-	47605	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:39
-	105	Joo.in. and (tft or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 16:39

-	13	(metal adj mask) and "t-shaped" and (co or cobalt or ta or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:11
-	2	"t-shaped" adj etching adj mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:26
-	1	"5452164".PN.	USPAT	2003/07/18 10:28
-	1	6303392.URPN.	USPAT	2003/07/18 10:28
-	9	("4814258"   "4859573"   "4988609"   "5468595"   "5658469"   "5725997"   "5885749"   "6042975"   "6303392").PN.	USPAT	2003/07/18 10:32